

# **MOSFET** – N-Channel, **SOT-23**

2.8 A, 20 V

## MGSF2N02EL, MVSF2N02EL

These miniature surface mount MOSFETs low  $R_{DS(on)}$  assure minimal power loss and conserve energy, making these devices ideal for use in space sensitive power management circuitry.

#### **Features**

- Low R<sub>DS(on)</sub> Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space
- I<sub>DSS</sub> Specified at Elevated Temperature
- AEC Q101 Qualified and PPAP Capable MVSF2N02EL
- These Devices are Pb-Free and are RoHS Compliant

## **Applications**

- DC-DC Converters
- Power Management in Portable and Battery Powered Products, ie: Computers, Printers, PCMCIA Cards, Cellular and Cordless Telephones

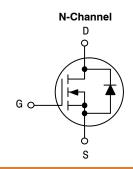
## MAXIMUM RATINGS (T<sub>J</sub> = 25 °C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	20	Vdc
Gate-to-Source Voltage - Continuous	V <sub>GS</sub>	± 8.0	Vdc
Drain Current - Continuous @ $T_A$ = 25 °C - Single Pulse ( $t_p$ = 10 $\mu$ s)	I <sub>D</sub> I <sub>DM</sub>	2.8 5.0	A
Total Power Dissipation @ T <sub>A</sub> = 25°C	P <sub>D</sub>	1.25	W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	– 55 to 150	°C
Thermal Resistance Junction-to-Ambient (Note 1) Thermal Resistance Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	100 300	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T <sub>L</sub>	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. 1" Pad, t < 10 sec.
- 2. Min pad, steady state.

## 2.8 A, 20 V $R_{DS(on)} = 85 \text{ m}\Omega \text{ (max)}$



## MARKING DIAGRAM



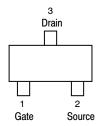
SOT-23 CASE 318 STYLE 21



XXX M

- = Specific Device Code
- = Date Code
- = Pb-Free Package

#### **PIN ASSIGNMENT**



## **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

## MGSF2N02EL, MVSF2N02EL

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C unless otherwise noted)

Characteristic			Min	Тур	Max	Unit
OFF CHARACTERISTICS		1		1	1	1
Drain-to-Source Breakdown Voltage (Note 3) ( $V_{GS}=0$ Vdc, $I_D=10~\mu Adc$ ) Temperature Coefficient (Positive)			20 -	_ 22	- -	Vdc mV/°C
Zero Gate Voltage Drain Current (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 Vdc) (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125 °C)			_ _	- -	1.0 10	μAdc
Gate-Source Leakage Current (V <sub>GS</sub>	= ± 8.0 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	_	_	±100	nA
ON CHARACTERISTICS (Note 3)		•		•		•
Gate-Source Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μAdc) Threshold Temperature Coefficient (Negative)			0.5 -	- -2.3	1.0 -	Vdc mV/°C
Static Drain-to-Source On-Resistance ( $V_{\rm GS}$ = 4.5 Vdc, $I_{\rm D}$ = 3.6 A) ( $V_{\rm GS}$ = 2.5 Vdc, $I_{\rm D}$ = 3.1 A)		R <sub>DS(on)</sub>	<u>-</u>	78 105	85 115	mΩ
DYNAMIC CHARACTERISTICS		•		•		•
Input Capacitance		C <sub>iss</sub>	-	150	-	pF
Output Capacitance	$(V_{DS} = 5.0 \text{ Vdc}, V_{GS} = 0 \text{ V}, \\ f = 1.0 \text{ MHz})$	C <sub>oss</sub>	-	130	-	1
Transfer Capacitance	,	C <sub>rss</sub>	ı	45	-	
SWITCHING CHARACTERISTICS (	Note 4)					
Turn-On Delay Time		t <sub>d(on)</sub>	ı	6.0	-	ns
Rise Time	(V <sub>DD</sub> = 16 Vdc, I <sub>D</sub> = 2.8 Adc,	t <sub>r</sub>	_	95	_	
Turn-Off Delay Time	$V_{gs} = 4.5 \text{ V}, R_{G} = 2.3 \Omega$	t <sub>d(off)</sub>	ı	28	1	
Fall Time		t <sub>f</sub>	_	125	_	
Gate Charge		Q <sub>T</sub>	-	3.5		nC
	$(V_{DS} = 16 \text{ Vdc}, I_D = 1.75 \text{ Adc}, V_{GS} = 4.0 \text{ Vdc}) \text{ (Note 3)}$	Q <sub>gs</sub>	-	0.6	-	
	, , ,	$Q_{gd}$	-	1.5	_	
SOURCE-DRAIN DIODE CHARACT	TERISTICS					
Forward Voltage	(I <sub>S</sub> = 1.0 Adc, V <sub>GS</sub> = 0 Vdc) (Note 3)	V <sub>SD</sub>	_ _	0.76 -	1.2	V
Reverse Recovery Time		t <sub>rr</sub>	_	104	-	ns
	$(I_S = 1.0 \text{ Adc}, V_{GS} = 0 \text{ Vdc},$	t <sub>a</sub>	-	42	-	1
	$dl_{S}/dt = 100 A/\mu s)$ (Note 3)	t <sub>b</sub>	-	62	_	1
Reverse Recovery Stored Charge	Charge		-	0.20	-	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MGSF2N02ELT1G	SOT-23	2 000 / Tono % Dool
MVSF2N02ELT1G*	(Pb-Free)	3,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*MVSF Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP

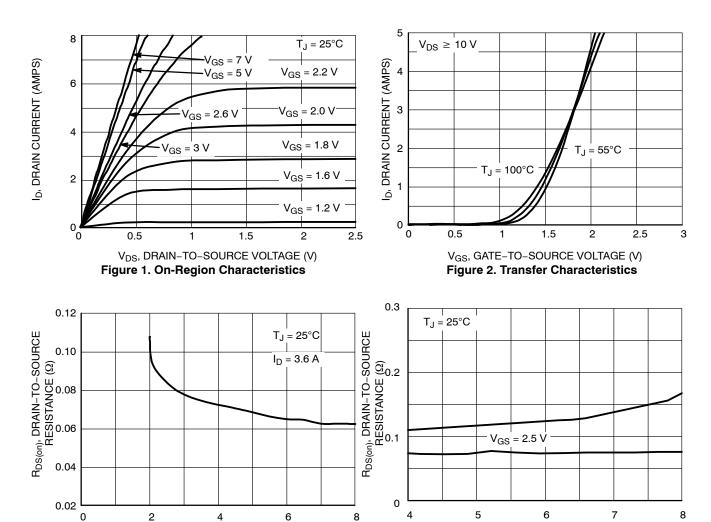
<sup>3.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

<sup>4.</sup> Switching characteristics are independent of operating junction temperature.

Capable.

## MGSF2N02EL, MVSF2N02EL

#### TYPICAL CHARACTERISTICS



 $\label{eq:VGS} V_{GS}, \text{GATE-TO-SOURCE VOLTAGE (V)}$  Figure 3. On-Resistance vs. Gate-to-Source Voltage

-I<sub>D</sub>, DRAIN CURRENTS (AMPS)

Figure 4. On-Resistance vs. Gate Voltage

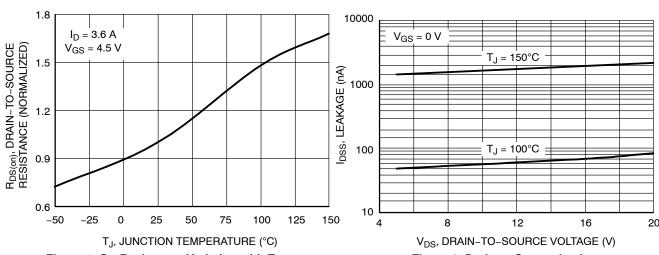


Figure 5. On-Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current vs. Voltage

## MGSF2N02EL, MVSF2N02EL

## **TYPICAL CHARACTERISTICS**

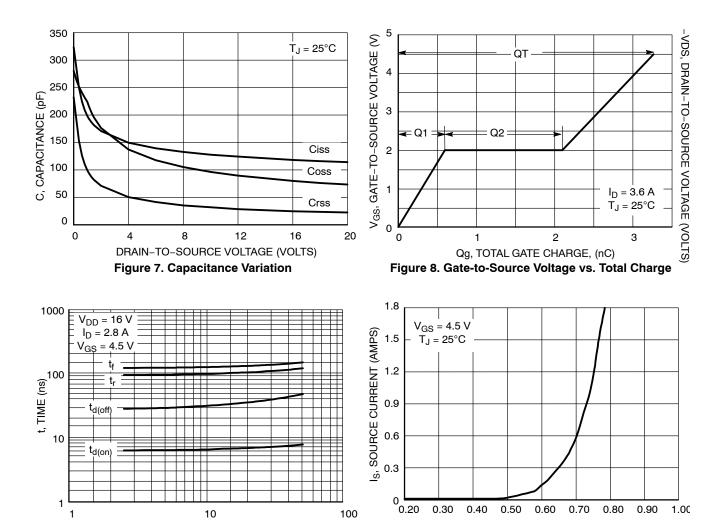


Figure 9. Resistive Switching Time Variation vs. **Gate Resistance** 

10  $R_G$ , GATE RESISTANCE  $(\Omega)$ 

Figure 10. Diode Forward Voltage vs. Current

0.50

0.60

V<sub>SD</sub>, SOURCE-TO-DRAIN VOLTAGE (V)

0.70

0.80

0.90

1.00

0.30

0.40

**MILLIMETERS** 

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

\_\_\_





### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 

MAX

1.11

0.10

0.50

0.20

3.04

1.40

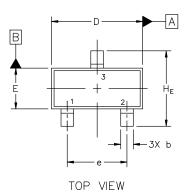
2.04

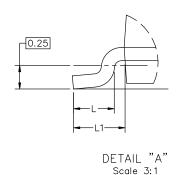
0.55

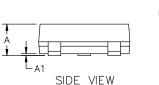
0.69

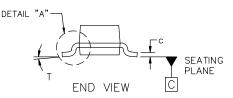
2.64

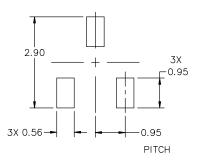
10°











#### NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package



\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

## SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODI	
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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